

Green Products

SB5150 SCHOTTKY RECTIFIER

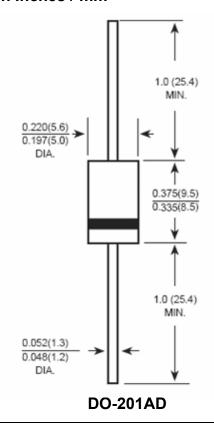
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Features:

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In Inches / mm



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Marking Diagram:



Where XXXXX is YYWWL

SB = Device Type

5 = Forward Current (5A) 150 = Reverse Voltage (150V)

SSG = SSG YY = Year WW = Week L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SB5150	DO-201AD (Pb-Free)	1250 pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	150	V
Max. Average Forward	I _{F(AV)}	50% duty cycle @T _C =105°C, rectangular wave form	5	А
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	120	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage	V_{F1}	@ 5A, Pulse, T _J = 25 °C	0.93	V
Drop(per leg)*	V_{F2}	@ 5A, Pulse, T _J = 125 °C	0.80	V
Max. Reverse Current at DC	I _{R1}	@V _R = rated VR	1	mA
condition		$T_J = 25 ^{\circ}C$		
Max. Reverse Current *	I_{R2}	@V _R = rated VR	7.0	mA
		T _J = 125 °C		
Max. Junction Capacitance	C_T	$@V_R = 5V, T_C = 25 ^{\circ}C$	200	pF
		$f_{SIG} = 1MHz$		
Typical Series Inductance	L_S	Measured lead to lead 5 mm	8.0	nΗ
		from package body		
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

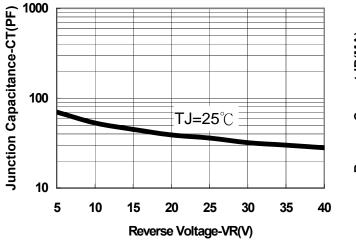
^{*} Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	°C
Max. Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	4.5	°C/W
Approximate Weight	wt	-	1.02	g
Case Style		DO-201AD		

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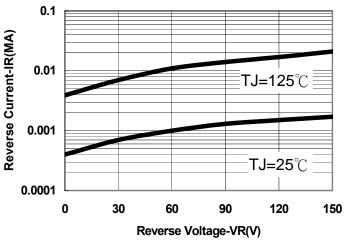


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

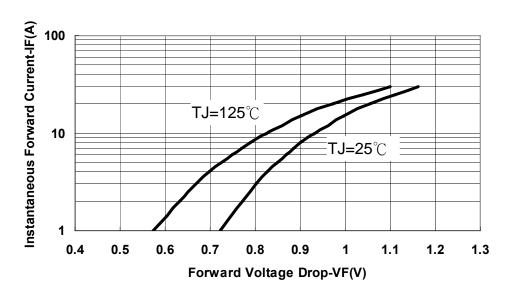


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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Technical Data Green Products Data Sheet N0093 Rev. -

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